



Information Disclosure Statement
USSN 10/776,862
August 10, 2004
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Form PTO-1449 (Modified) Page 1 of 2	ATTY DOCKET NO. B-4967NP 621679-8	U.S. SERIAL NO. 10/776,862
LIST OF PATENTS AND PUBLICATIONS STATEMENT	APPLICANTS Mary CHEN	
	FILING DATE February 10, 2004	GROUP <u>287</u> not yet assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	ISSUE DATE	NAME	CLASS	SUB- CLASS	FILING DATE or 102(e) DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO

EXAMINER <u>[Signature]</u>	DATE CONSIDERED <u>12/05</u>
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